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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
10/814,682	03/31/2004	Wen Lin	LIN 13-38	8308	
47396 HITT GAINES	7590 08/07/200 S PC	EXAMINER			
LSI Corporation	on	MALDONADO, JULIO J			
PO BOX 8325 RICHARDSO			ART UNIT	PAPER NUMBER	
iucii iuo 50	11, 111 75005		2823		
			NOTIFICATION DATE	DELIVERY MODE	
			08/07/2008	ELECTRONIC	

Please find below and/or attached an Office communication concerning this application or proceeding.

The time period for reply, if any, is set in the attached communication.

Notice of the Office communication was sent electronically on above-indicated "Notification Date" to the following e-mail address(es):

docket@hittgaines.com

Advisory Action Before the Filing of an Appeal Brief

Application No.	Applicant(s)					
10/814,682	LIN ET AL.					
Examiner	Art Unit					
JULIO J. MALDONADO	2823					

	JULIO J. MALDONADO	2823						
The MAILING DATE of this communication appe	ars on the cover sheet with the	correspondence add	ress					
THE REPLY FILED 02 July 2008 FAILS TO PLACE THIS APPL	ICATION IN CONDITION FOR AL	LOWANCE.						
 M The reply was filed after a final rejection, but prior to or on application, applicant must timely file one of the following i application in condition for allowance; (2) a Notice of Appe for Continued Examination (RCE) in compliance with 37 C periods: 	the same day as filing a Notice of replies: (1) an amendment, affidavi eal (with appeal fee) in compliance	Appeal. To avoid abar t, or other evidence, w with 37 CFR 41.31; or	hich places the (3) a Request					
a) The period for reply expires 2 months from the mailing date the period for reply expires on: (1) the mailing date of the no event, however, will the statutory period for reply expire to Examiner Note: If box 1 is checked, check either box (a) or (MONTHS OF THE FINAL REJECTION, See MPEP 766.07()	dvisory Action, or (2) the date set forth ater than SIX MONTHS from the mailing b). ONLY CHECK BOX (b) WHEN THE	date of the final rejection	n.					
Extensions of time may be obtained under 37 CFR 1.136(a). The date have been filled is the date for purposes of determining the period of under 37 CFR 1.17(a) is calculated from: (1) the expiration date of the set forth in (b) above, if checked. Any reply received by the Office may reduce any earned patent term adjustment. See 37 CFR 1.704(b). NOTICE OF APPEAL.	on which the petition under 37 CFR 1.1 ension and the corresponding amount hortened statutory period for reply origi than three months after the mailing dat	of the fee. The appropria nally set in the final Office	ate extension fee e action; or (2) as					
The Notice of Appeal was filed on A brief in comp filing the Notice of Appeal (37 CFR 41.37(a)), or any exter Notice of Appeal has been filed, any reply must be filed wi AMENDMENTS	sion thereof (37 CFR 41.37(e)), to	avoid dismissal of the						
 The proposed amendment(s) filed after a final rejection, to (a) They raise new issues that would require further corton. (b) They raise the issue of new matter (see NOTE below) 	nsideration and/or search (see NO w);	ΓE below);						
(c) They are not deemed to place the application in beti appeal; and/or (d) They present additional claims without canceling a company of the present additional claims without canceling a company of the present additional claims without canceling a company of the present additional claims without canceling a company of the present additional claims without canceling a company of the present additional claims without canceling a company of the present additional claims.			ie issues ioi					
NOTE: (See 37 CFR 1.116 and 41.33(a)).	corresponding number or initially reju	otod oldiirio.						
4. The amendments are not in compliance with 37 CFR 1.12		mpliant Amendment (I	PTOL-324).					
7. If or purposes of appeal, the proposed amendment(s): a) I how the new or amended claims would be rejected is prov. The status of the claim(s) is (or will be) as follows: Claim(s) allowed:		I be entered and an e	xplanation of					
AFFIDAVIT OR OTHER EVIDENCE								
 The affidavit or other evidence filed after a final action, but because applicant failed to provide a showing of good and was not earlier presented. See 37 CFR 1.116(e). 								
 The affidavit or other evidence filed after the date of filing entered because the affidavit or other evidence failed to o showing a good and sufficient reasons why it is necessary 	vercome <u>all</u> rejections under appea	al and/or appellant fail:	s to provide a					
 The affidavit or other evidence is entered. An explanation REQUEST FOR RECONSIDERATION/OTHER 	n of the status of the claims after er	ntry is below or attach	ed.					
11. \(\) The request for reconsideration has been considered but does NOT place the application in condition for allowance because: See Continuation Sheet.								
12. Note the attached Information <i>Disclosure Statement</i> (s). (13. Other:	PTO/SB/08) Paper No(s).							
/Matthew S. Smith/ Supervisory Patent Examiner, Art Unit 2823	Julio J. Maldonado Art Unit: 2823							

U.S. Patent and Trademark Office PTOL-303 (Rev. 08-06)

Continuation of 11. does NOT place the application in condition for allowance because: Applicant's arguments filed 07/02/2008 have been fully considered but they are not persuasive.

Applicants argue, "...the Examiner points the Applicants to FIG. 4 of Liaw, and the associated text at column 6, lines 17-39 therein. The Applicants respectfully disagreed with the Examiner that FIG. 4, and the associated text, teached called the signature of or sourcedrain regions located within a doped epitaxial layer proximate a gate structure, wherein the sourcedrain regions do not extend into a co-doped germanium buried layer located thereunder, as is presently claimed. For instance, all the text associated with FIG. 4 is directed to a SIC buried layer. Nothing in that text teaches or suggests that the SIC buried layer could be a co-doped germanium buried layer, as is presently claimed..."

In response to this argument, Liaw is directed to a semiconductor device including a buried epitaxial layer and a second epitaxial layer on top of said buried epitaxial layer, wherein said buried epitaxial layer and proper to different thicknesses of these epitaxial layers in order to achieve a certain level of strain that would obviously influence the performance to the device. In both embodiments of Liaw (See Figs. 1 and 4 and related text), there are source/drain regions, gate regions, channel regions, a top the precipion of the properties of the embodiment of the invention (Fig.1), the source/drain regions extend to the buried region and in the second embodiment (Fig.4), the source/drain regions does not extend to the buried region.